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2-Bit Translating Bus Switch

7WBD3125

The 7WBD3125 is an advanced high-speed low-power 2-bit translating bus switch in ultra-small footprints.

Features

- High Speed: $t_{PD} = 0.25 \text{ ns (Max)} @ V_{CC} = 4.5 \text{ V}$
- 3 Ω Switch Connection Between 2 Ports
- Power Down Protection Provided on Inputs
- Zero Bounce
- TTL-Compatible Control Inputs
- Ultra-Small Pb-Free Packages
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices



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MARKING DIAGRAMS



UDFN8 MU SUFFIX CASE 517AJ





UDFN8 1.95 x 1.0 CASE 517CA





Micro8 DM SUFFIX CASE 846A





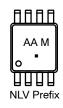
UQFN8 MU SUFFIX CASE 523AN





US8 US SUFFIX CASE 493





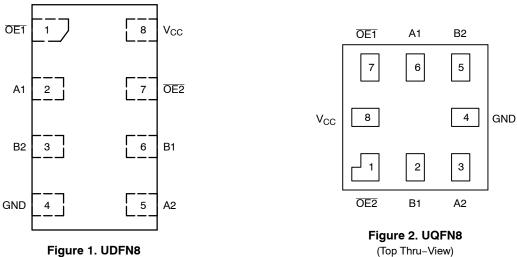
AF, X, D125, AE, AA = Specific Device Code
M = Date Code
A = Assembly Location

L = Lot Code
Y = Year Code
W = Week Code
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.



(Top Thru-View)

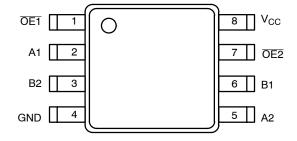


Figure 3. US8/Micro8 (Top View)

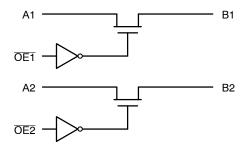


Figure 4. Logic Diagram

FUNCTION TABLE

| Input OEn | Function | |
|-----------|------------|--|
| L | Bn = An | |
| Н | Disconnect | |

MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit | |
|----------------------|---|--|---------------------------|------|--|
| V _{CC} | DC Supply Voltage | | -0.5 to +7.0 | V | |
| V _{IN} | Control Pin Input Voltage | | -0.5 to +7.0 | V | |
| V _{I/O} | Switch Input / Output Voltage | | -0.5 to +7.0 | V | |
| I _{IK} | Control Pin DC Input Diode Current | V _{IN} < GND | -50 | mA | |
| I _{OK} | Switch I/O Port DC Diode Current | V _{I/O} < GND | -50 | mA | |
| Io | ON-State Switch Current | | ± 128 | mA | |
| | Continuous Current Through V _{CC} or GND | | ± 150 | mA | |
| Icc | DC Supply Current Per Supply Pin | | ± 150 | mA | |
| I _{GND} | DC Ground Current per Ground Pin | | ± 150 | mA | |
| T _{STG} | Storage Temperature Range | -65 to +150 | °C | | |
| TL | Lead Temperature, 1 mm from Case for 10 Second | nds | 260 | °C | |
| TJ | Junction Temperature Under Bias | | 150 | °C | |
| θ _{JA} | Thermal Resistance | US8 (Note 1) UDFN8 UQFN8 Micro8 | 251 111 208 392 | °C/W | |
| P _D | Power Dissipation in Still Air at 85°C | US8 UDFN8 UQFN8 Micro8 | 498 1127 601 319 | mW | |
| MSL | Moisture Sensitivity | | Level 1 | | |
| F _R | Flammability Rating Oxygen Index: 28 to 34 | | UL 94 V-0 @ 0.125 in | | |
| V _{ESD} | ESD Withstand Voltage Human Body Mode (Note 2) Machine Model (Note 3) Charged Device Model (Note 4) | | > 2000 > 200 N/A | V | |
| I _{LATCHUP} | Latchup Performance Above V _{CC} and Below GN | D at 125°C (Note 5) | ±200 | mA | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
- 2. Tested to EIA / JESD22-A114-A.
- 3. Tested to EIA / JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|------------------|---|-----|---------|------|
| V _{CC} | Positive DC Supply Voltage | 4.0 | 5.5 | V |
| V _{IN} | Control Pin Input Voltage | 0 | 5.5 | V |
| V _{I/O} | Switch Input / Output Voltage | 0 | 5.5 | V |
| T _A | Operating Free-Air Temperature | -55 | +125 | °C |
| Δt / ΔV | Input Transition Rise or Fall Rate Control Input Switch I/O | 0 | 5 DC | nS/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

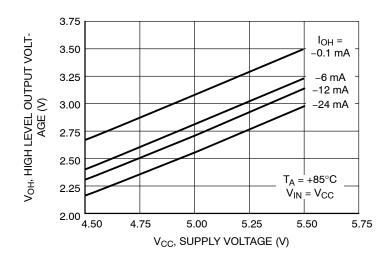
| | | | V _{CC} | | T _A = 25°(| C | T _A –55°C to | | |
|------------------|---|--|-----------------|-----|-----------------------|--------------|----------------------------|--------------|----------|
| Symbol | Parameter | Conditions | (V) | Min | Тур | Max | Min | Max | Unit |
| V _{IK} | Clamp Diode Voltage | I _{I/O} = -18 mA | 4.5 | | | -1.2 | | -1.2 | V |
| V _{IH} | High-Level Input Voltage (Control) | | 4.0 to 5.5 | 2.0 | | | 2.0 | | V |
| V _{IL} | Low-Level Input Voltage (Control) | | 4.0 to 5.5 | | | 0.8 | | 0.8 | V |
| V _{OH} | Output Voltage High | See Figure 5 | | | | | | | |
| I _{IN} | Input Leakage Current | $0 \le V_{IN} \le 5.5 V$ | 5.5 | | | ±0.1 | | ±1.0 | μΑ |
| l _{OFF} | Power Off Leakage Current | V _{I/O} = 0 to 5.5 V | 0 | | | ±0.1 | | ±1.0 | μΑ |
| I _{CC} | Quiescent Supply Current | | 5.5 | | | ±1.0 ±0.1 | | ±1.0 ±1.0 | mA μA |
| Δl _{CC} | Increase in Supply Current (Control Pin) | One input at 3.4 V; Other inputs at V _{CC} or GND | 5.5 | | | | | 2.5 | mA |
| R _{ON} | Switch ON Resistance | $V_{I/O} = 0,$ $I_{I/O} = 64 \text{ mA}$ $I_{I/O} = 30 \text{ mA}$ | 4.5 | | 3 3 | 7 7 | | 7 7 | Ω |
| | | $V_{I/O} = 2.4,$ $I_{I/O} = 15 \text{ mA}$ | | | 15 | 50 | | 50 | |
| | | $V_{I/O} = 2.4,$ $I_{I/O} = 15 \text{ mA}$ | 4.0 | | 50 | 70 | | 70 | |

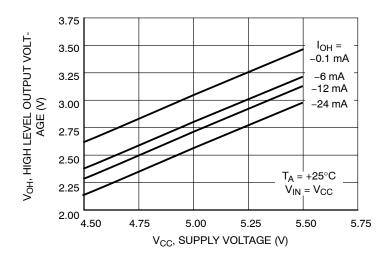
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS

| | | | V _{CC} | T _A = 25 °C | | T _A = -55°C to +125°C | | | |
|----------------------|-------------------------------|----------------------------|-----------------|------------------------|-----|-------------------------------------|-----|------|------|
| Symbol | Parameter | Test Condition | (V) | Min | Тур | Max | Min | Max | Unit |
| t _{PD} | Propagation Delay, Bus to Bus | See Figure 6 | 4.0 to 5.5 | | | 0.25 | | 0.25 | ns |
| t _{EN} | Output Enable Time | See Figure 6 | 4.5 to 5.5 | 0.8 | 2.5 | 4.2 | 0.8 | 4.2 | ns |
| | | | 4.0 | 0.8 | 3.0 | 4.6 | 0.8 | 4.6 | |
| t _{DIS} | Output Disable Time | | 4.5 to 5.5 | 0.8 | 3.0 | 4.8 | 0.8 | 4.8 | ns |
| | | | 4.0 | 0.8 | 2.9 | 4.4 | 0.8 | 4.4 | |
| C _{IN} | Control Input Capacitance | V _{IN} = 5 or 0 V | 5.0 | | 2.5 | | | | pF |
| C _{IO(ON)} | Switch On Capacitance | Switch ON | 5.0 | | 10 | | | | pF |
| C _{IO(OFF)} | Switch Off Capacitance | Switch OFF | 5.0 | | 5 | | | | pF |

TYPICAL DC CHARACTERISTICS





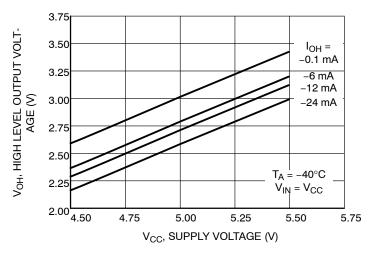
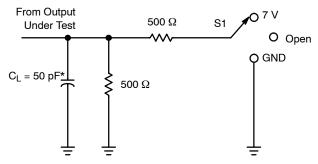


Figure 5. Output Voltage High vs Supply Voltage

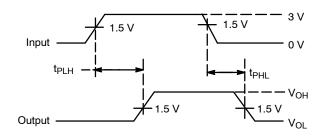
AC LOADING AND WAVEFORMS

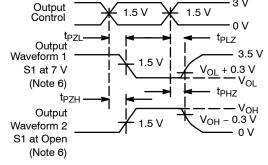
Parameter Measurement Information



| Test | S1 |
|------------------------------------|------|
| t _{PD} | Open |
| t _{PLZ} /t _{PZL} | 7 V |
| t _{PHZ} /t _{PZH} | Open |

^{*}CL includes probes and jig capacitance.





Voltage Waveforms Propagation Delay Times

Voltage Waveforms Enable and Disable Times

- 6. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control
- 7. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_0 = 50 Ω , $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns. 8. The outputs are measured one at a time, with one transition per measurement.
- 9. t_{PLZ} and t_{PHZ} are the same as t_{DIS}.
- 10. t_{PZL} and t_{PZH} are the same as t_{EN}.
 11. t_{PHL} and t_{PLH} are the same as t_{PD}.

Figure 6. t_{PD}, t_{EN}, t_{DIS} Loading and Waveforms

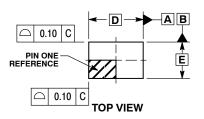
ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------|--------------------------------------|-----------------------|
| 7WBD3125USG | US8 (Pb-Free) | 3000 / Tape & Reel |
| NLV7WBD3125USG* | US8 (Pb-Free) | 3000 / Tape & Reel |
| 7WBD3125MUTAG | UDFN8 (Pb-Free) | 3000 / Tape & Reel |
| 7WBD3125AMUTCG | UQFN8 (Pb-Free) | 3000 / Tape & Reel |
| 7WBD3125DMR2G | Micro8 (Pb-Free) | 4000 / Tape & Reel |
| 7WBD3125DMUTCG | UDFN8, 1.95 x 1.0, 0.5P (Pb-Free) | 3000 / Tape & Reel |

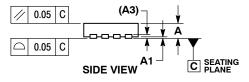
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

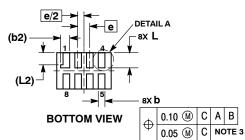
PACKAGE DIMENSIONS

UDFN8 1.8 x 1.2, 0.4P CASE 517AJ ISSUE O





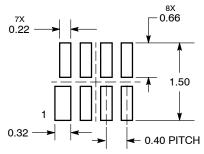




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
 4. MOLD FLASH ALLOWED ON TERMINALS ALONG EOGE OF PACKAGE, FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
 5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

| | MILLIMETERS | | | | |
|-----|-------------|------|--|--|--|
| DIM | MIN | MAX | | | |
| Α | 0.45 | 0.55 | | | |
| A1 | 0.00 | 0.05 | | | |
| A3 | 0.127 | REF | | | |
| b | 0.15 0.25 | | | | |
| b2 | 0.30 | REF | | | |
| D | 1.80 | BSC | | | |
| E | 1.20 | BSC | | | |
| е | 0.40 | BSC | | | |
| L | 0.45 | 0.55 | | | |
| L1 | 0.00 | 0.03 | | | |
| L2 | 0.40 REF | | | | |

MOUNTING FOOTPRINT* SOLDERMASK DEFINED

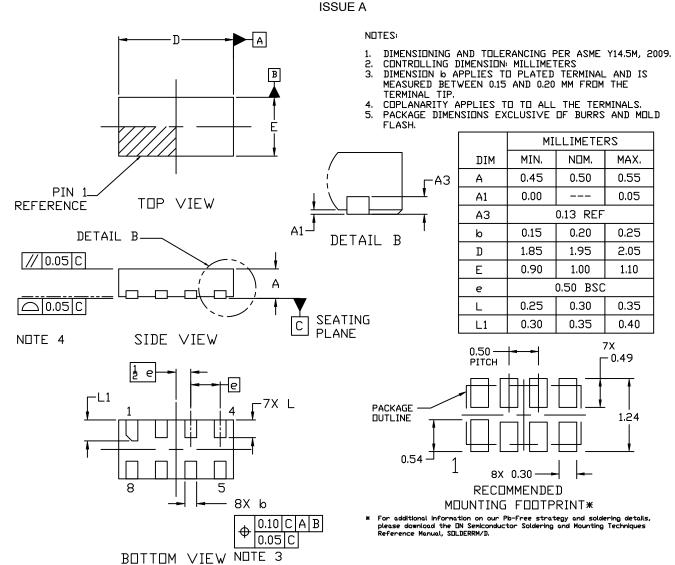


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

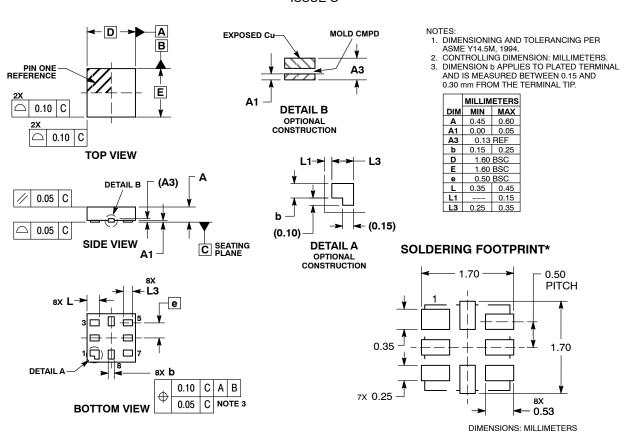
PACKAGE DIMENSIONS

UDFN8 1.95x1.0, 0.5P CASE 517CA



PACKAGE DIMENSIONS

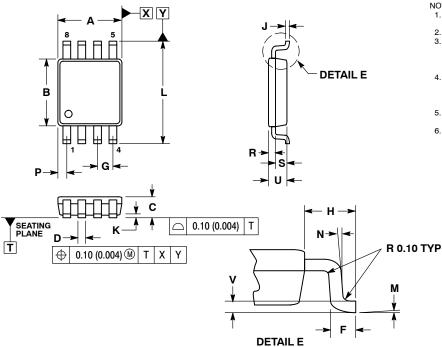
UQFN8, 1.6x1.6, 0.5P CASE 523AN ISSUE O



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

US8 **CASE 493** ISSUE D



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

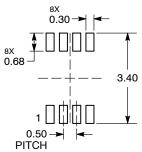
 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURR. MOLD FLASH. PROTRUSION AND GATE BURR SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH AND PROTRUSION. INTERLEAD FLASH AND PROTRUSION SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.
- AND PHOTHOSION SHALL NOT EXCEED 0.14MM (0.0055") PER SIDE.
 LEAD FINISH IS SOLDER PLATING WITH
 THICKNESS OF 0.0076-0.0203MM (0.003-0.008").
 ALL TOLERANCE UNLESS OTHERWISE
 SPECIFIED ±0.0508MM (0.0002").

| | MILLIMETERS | | INC | HES | |
|-----|-------------|------|-----------|-------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 1.90 | 2.10 | 0.075 | 0.083 | |
| В | 2.20 | 2.40 | 0.087 | 0.094 | |
| С | 0.60 | 0.90 | 0.024 | 0.035 | |
| D | 0.17 | 0.25 | 0.007 | 0.010 | |
| F | 0.20 | 0.35 | 0.008 | 0.014 | |
| G | 0.50 | BSC | 0.020 | BSC | |
| Н | 0.40 | REF | 0.016 | REF | |
| J | 0.10 | 0.18 | 0.004 | 0.007 | |
| K | 0.00 | 0.10 | 0.000 | 0.004 | |
| L | 3.00 | 3.20 | 0.118 | 0.128 | |
| М | 0 ° | 6° | 0 ° | 6° | |
| N | 0 ° | 10 ° | 0 ° | 10 ° | |
| Р | 0.23 | 0.34 | 0.010 | 0.013 | |
| R | 0.23 | 0.33 | 0.009 | 0.013 | |
| S | 0.37 | 0.47 | 0.015 | 0.019 | |
| U | 0.60 | 0.80 | 0.024 | 0.031 | |
| ٧ | 0.12 | BSC | 0.005 BSC | | |

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.